

PHOTORESIST STRIP METHOD

ABSTRACT

An improved method for removing a photoresist mask from an etched aluminum pattern after etching the pattern in a chlorine containing plasma has been created. The method is a two step process, in which a first stripping step is in a plasma containing O_2 and H_2O and a second stripping step is in a plasma containing O_2 .

(FIGURE 2 IS SUGGESTED FOR PUBLICATION)